JC872 U.S. PTO
09/887910
06/22/01

Class	Subclass

ISSUE CLASSIFICATION

PATENT NUMBER

U.S. **UTILITY** Patent Application

O.I.P.E.	PATENT DATE
SCANNED Eleb Q.A. TM	

APPLICATION NO.	CONT/PRIOR	CLASS	SUBCLASS	ART UNIT	EXAMINER
09/887910		438		2812	Anya

APPLICANTS: Jack Hwang
Mitchell Taylor

TITLE: Method of making a semiconductor transistor by implanting ions into a gate dielectric layer thereof

PTO-2040
12/99

ISSUING CLASSIFICATION

ORIGINAL		CROSS REFERENCE(S)	
CLASS	SUBCLASS	CLASS	SUBCLASS (ONE SUBCLASS PER BLOCK)

INTERNATIONAL CLASSIFICATION

☐ Continued on Issue Slip Inside File Jacket

☐ TERMINAL DISCLAIMER	DRAWINGS			CLAIMS ALLOWED	
	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims	Print Claim for O.G.
☐ The term of this patent subsequent to _____ (date) has been disclaimed.	_____ (Assistant Examiner)		_____ (Date)	NOTICE OF ALLOWANCE MAILED	
☐ The term of this patent shall not extend beyond the expiration date of U.S Patent. No. _____	_____ (Primary Examiner)		_____ (Date)	ISSUE FEE	
				Amount Due	Date Paid